

AMENDMENT TO THE CLAIMS

**In the Claims**

Please CANCEL claims 8-16, 19 and 25-32; and

Please AMEND claims 33 and 34 as follows:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-16 (Canceled).

17. (Previously Presented) A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate;

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack;

forming a spacer adjacent a sidewall of the gate stack; and

etching upper portions of the spacer to form sidewalls only at a lower portion of the gate stack.

Claims 18-32 (Canceled).

33. (Currently Amended) The method of claim 8, further comprising A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate;

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack; and

depositing a salicide gate region on top of the gate stack,

wherein a gate is about 60 nm wide, a spacer is about 50 nm wide, and the nitride film provides a stress of about 2.0 GPa, the enhanced stress in the transistor channel is greater than approximately  $4.5 \times 10^9$  dynes/cm<sup>2</sup> at about 5 nm below a gate oxide.

34. (Currently Amended) The method of claim 8, A method of enhancing stress in a semiconductor device, comprising:

depositing a layer of nitride film over a gate stack and a surface of a substrate; and

removing the nitride film on the gate stack to provide enhanced stress in a transistor channel under the gate stack,

wherein a gate is about 60 nm wide, a spacer is about 50 nm wide, and the nitride film provides a stress of about 2.0 GPa, the enhanced stress in the transistor channel is greater than approximately  $4.5 \times 10^9$  dynes/cm<sup>2</sup> at about 5 nm below a gate oxide, and

wherein the substrate remains covered by the nitride film after the nitride film is removed from an upper portion of the gate stack.